Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7430	pixel near10 drain near10 contact	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/20 15:14
L2	3150	(pixel near10 drain near10 contact) and "349"/\$.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/20 15:15
L3	2662	(pixel near10 drain near10 (contact adj hole)) and "349"/\$.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/20 15:16
L4	1126	(pixel near10 drain near10 (contact adj hole)) and "349"/\$.ccls.	USPAT	OR	ON	2007/11/20 15:17
L5	1087	((pixel adj electrode) near10 drain near10 (contact adj hole)) and "349"/\$.ccls.	USPAT	OR	ON	2007/11/20 15:17
L6	265	((pixel adj electrode) near10 drain near10 (contact adj hole)) and direct and "349"/\$.ccls.	USPAT	OR	ON	2007/11/20 15:25
L7	0	((pixel adj electrode) near10 drain near10 (connect with direct)) and "349"/\$.ccls.	USPAT	OR	ON	2007/11/20 15:26
L8	279	((pixel adj electrode) near10 drain near10 connect) and "349"/\$.ccls.	USPAT	OR	ON	2007/11/20 15:47
L9	21	((pixel adj electrode) near10 drain near10 connect) and "349"/\$.ccls. and (without near10 hole)	USPAT	OR ,	ON .	2007/11/20 15:48
L10	28	cutting-off adj plate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/20 16:01

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L11	332	(cutting-off) near10 plate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/20 16:02
S48	927	349/149	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR ·	ON	2005/12/15 13:31
S49	963	349/187	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:26
S50	27	cutting-off adj plate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 14:54
S51	4883	expos\$4 near10 pad near10 etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 15:38
S52	. 237	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 11:15

S53	239	("1954691"	"2851408"	"2867541"	US-PGPUB;	OR	OFF	2005/05/19 16:28	
			-	"3108904"	USPAT;				
				"3360450" j	USOCR				
			3554889"	•					
	;		3755704"						
			•	•					
			"3947716"						
			"4008412"	•					
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			"4164680"	•					
			"4307507"	•					
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			"4498952"	•					
	1		"4513308"	•					ľ
			"4578614"						
			"4633131"	•					
			"4684353"	•					
:			"4687825"						
			"4721885"		*				
	'		"4763187"	•	,				1
			"4816717"	•					
			<b>"4</b> 827177"						
- 25			"4855636"			=			
		"4857799"	"4874981"	"4882659"					
		"4889690"	"4892757"	"4899081"					
		"4900584"	"4908539"	"4923421"	,				
		"4926056"	"4933108"	"4940916"					
		"4943343"	"4956202"	"4956574"					
		"4964946"	"4987007"	"4990416"					
		"4990766"	"4994205"	"5007873"	.				
		"5015912"	"5019003"	"5036247"			•	٠,	
			"5043715"	"5054046"		.v			
		"5054047"		"5055744"					
		"5057047"	•	"5063327"					
		"5064396"	•	"5075591"				•	
		"5075595"	"5075596"	"5079476"					
		"5085958"	"5089292"	"5089742"					
		"5089812"	l "5090932"	"5098737"					
	:	ł .	5101288"	"5103144"					
		"5103145"	"5117267"	"5117299"					
		"5119386"	"5123039"	"5124072"					
		"5124558"	"5126287"	"5129850"					-
		"5132585"		•				1	Ì
		("5136764"		,					
	*	"5141459"	"5141460"	"5142184"					ŀ
		"5142256"	"5142390"	"5144191"					
		"5148078"	"5148461"	"5150011"				,	
		"5150192"	"5151061"	"5153753"					
		"5153901"	"5155420"	"5156770"					
		"5157304"	"5157309"	"5162704"					
		"5166456"	"5173634"	"5173635"				•	
		"5173697"	"5180951"	"5183529"		,			
-		"5185178"	"5186670"	"5187578"					
		"5191217"	"5192240"	"5194780"					
	1	"5199917"	"5192240   "5199918"	"5201992"				•	
		"5202571"	"5203731"	"5204021"					
		"5204581"	3203731   "5205770"	320 <del>1</del> 021    -"5209687"	<u> </u>	,			Ì
11/20/0	7 4:16:32 PM		L"5210462"					Page 3	3
C:\Docu	ments and Sel	triug \$ DA QUKIN	Počijtžýžve/	ŶSŢŢŶŶŎŢŔŹĬŶĠſĠs\	10713198[cuttin	g_off_plate_o	ry_etchin	].wsp	
	1	0220, 12	"521 1370   "5220725"	3217377     "5227699"	]				
		-,			·				•

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S54	24	(expos\$4 near10 pad near10 (dry adj etch\$4)) and gate and data and semiconductor and pixel and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 16:29
S55	94	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and cut\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2005/05/20 11:08
S56	2	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and cut\$4-off	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:08
S57	998	349/143	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:24
S58	367	349/150	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:24
S59	1653	349/43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:25
S60	357	349/43 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S61	73	349/150 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33

S62	131	349/152 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S63	114	349/143 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21
S65	84	349/143 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S67		349/152 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S69	291	349/43 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:39
S70	111	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and ((mask cutting-off) near10 metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:08
S71	9	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and ((mask cutting-off) near10 metal) and ((three "3") adj mask\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 12:54
S72	1857216	(dry adj etch\$4) nea10 insulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:11

S73	4990943	S72 (liquid adh crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR ·	ON	2005/05/23 17:10
S74	2348219	S72 (liquid adh crystal) and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:10
S75	150088	(dry adj etch\$4) nea10 insulat\$4 near10 expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/05/23 17:15
S76	11537	S75 and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:12
S77	2992	(S75 near10 remov\$4)and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:13
S78	833	(S75 near10 remov\$4)and (liquid adj crystal) and pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:13
S79	228	(S75 near10 remov\$4)and (liquid adj crystal) and (gate adj pad) and (data adj pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:14
S80	1281	(dry adj etch\$4) near10 insulat\$4 near10 expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/05/23 17:15

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S81	40	(dry adj etch\$4) near10 insulat\$4 near10 expos\$4 and (gate adj pad) and (data adj pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:16
S82	401	349/43 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S83	155	349/152 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S84	96	349/143 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S85	86	349/150 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR ·	ON	2005/12/15 13:33
S86	80	349/152 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S88	146	349/143 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21
S89	425	349/43 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21

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S90	1193	349/187	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21
S91	1096	349/187 and @ad<"20031117"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:26
S92	493	349/187 and @ad<"20031117" and mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:34
S93	508	349/187 and @ad<"20031117" and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:36
S94	605	"349"/\$.ccls. and @ad<"20031117" and mask\$4 and gate and data and pad and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:41
S95	104	"349"/\$.ccls. and @ad<"20031117" and mask\$4 and gate and data and pad and pixel and (thin adj film adj transistor adj array)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 16:16
S96	565	"349"/\$.ccls. and @ad<"20031117" and mask\$4 and gate and data and pad and pixel and ((thin adj film adj transistor adj array) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/04/09 17:21
S97	. 67	"349"/\$.ccls. and @ad<"20031117" and mask\$4 and gate and data and pad and pixel and ((thin adj film adj transistor adj array) TFT) and (cut\$4 near10 off)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 16:55

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S98	22	"349"/\$.ccls. and @ad<"20031117" and mask\$4 and gate and data and pad and pixel and ((thin adj film adj transistor adj array) TFT) and (cut\$4 near10 off) and protect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 16:56
S99	129454	((protect\$4 passivation) near10 substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:22
S10 0	8486	S99 and (liquid adj crystal) and (mask cutt\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:25
S10 1	3687	S100 and gate and data	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/04/09 17:24
S10 2	3387	S100 and gate and data and pixel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2007/04/09 17:25
S10 3	13	S99 and (liquid adj crystal) and mask and cutt\$4-off	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:26
S10 4	7424	S99 and (liquid adj crystal) and mask	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:26

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S10 5	2114	S99 and (liquid adj crystal) and mask and pad	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:26
S10 6	1031	S99 and (liquid adj crystal) and mask and pad and cut\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:26
S10 7	930	S99 and (liquid adj crystal) and mask and pad and cut\$4 and etch\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:27
\$10 8	405	S99 and (liquid adj crystal) and (mask with process) and pad and cut\$4 and etch\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR Jan	ON	2007/04/09 17:29
S10 9	19	S99 and (liquid adj crystal) and (mask with process) and pad and (cut\$4 with plate) and etch\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:28
S11 0	261	S99 and (liquid adj crystal) and (mask with process) and pad and cut\$4 and etch\$4 and @ad<"20031117"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ÖN	2007/04/09 17:29
S11 1	28	cutting-off adj plate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2007/11/20 16:01